

General Description

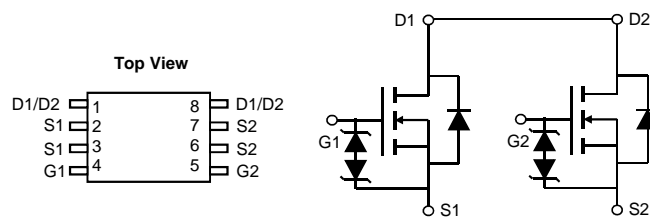
The AO8820 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

Features

| | |
|----------------------------------|----------------|
| V_{DS} | 20V |
| I_D (at $V_{GS}=10V$) | 7A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | < 21m Ω |
| $R_{DS(ON)}$ (at $V_{GS}=4.5V$) | < 24m Ω |
| $R_{DS(ON)}$ (at $V_{GS}=3.6V$) | < 28m Ω |
| $R_{DS(ON)}$ (at $V_{GS}=2.5V$) | < 32m Ω |
| $R_{DS(ON)}$ (at $V_{GS}=1.8V$) | < 50m Ω |



ESD protected!



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|----------------|------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current | I_D | $T_A=25^\circ\text{C}$ | 7 |
| | | $T_A=70^\circ\text{C}$ | 5.5 |
| Pulsed Drain Current ^C | I_{DM} | 30 | A |
| Power Dissipation ^B | P_D | $T_A=25^\circ\text{C}$ | 1.5 |
| | | $T_A=70^\circ\text{C}$ | 0.96 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|---------------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 64 | 83 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Ambient ^{A,D} | | Steady-State | 89 | 120 |
| Maximum Junction-to-Lead | $R_{\theta JL}$ | 53 | 70 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|--|-----|------|--------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 20 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =16V, V _{GS} =0V T _J =55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} = ±10V | | | 10 | μA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 0.5 | 0.8 | 1.1 | V |
| I _{D(ON)} | On state drain current | V _{GS} =10V, V _{DS} =5V | 30 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =7A T _J =125°C | 13 | 17.2 | 21 | mΩ |
| | | V _{GS} =4.5V, I _D =6.6A | 15 | 19.4 | 24 | |
| | | V _{GS} =3.6V, I _D =6A | 16 | 20.7 | 28 | |
| | | V _{GS} =2.5V, I _D =5.5A | 18 | 25 | 32 | |
| | | V _{GS} =1.8V, I _D =2A | | 35 | 50 | |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =7A | | 25 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.65 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 2.5 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =10V, f=1MHz | | 500 | | pF |
| C _{oss} | Output Capacitance | | | 100 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 52 | | pF |
| SWITCHING PARAMETERS | | | | | | |
| Q _g | Total Gate Charge | V _{GS} =4.5V, V _{DS} =10V, I _D =7A | | 6 | 9 | nC |
| Q _{gs} | Gate Source Charge | | | 2 | | nC |
| Q _{gd} | Gate Drain Charge | | | 1 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =5V, V _{DS} =10V, R _L =1.4Ω, R _{GEN} =3Ω | | 0.2 | | us |
| t _r | Turn-On Rise Time | | | 1.5 | | us |
| t _{D(off)} | Turn-Off DelayTime | | | 7.4 | | us |
| t _f | Turn-Off Fall Time | | | 18 | | us |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =7A, dI/dt=100A/μs | | 9 | | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =7A, dI/dt=100A/μs | | 10 | | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

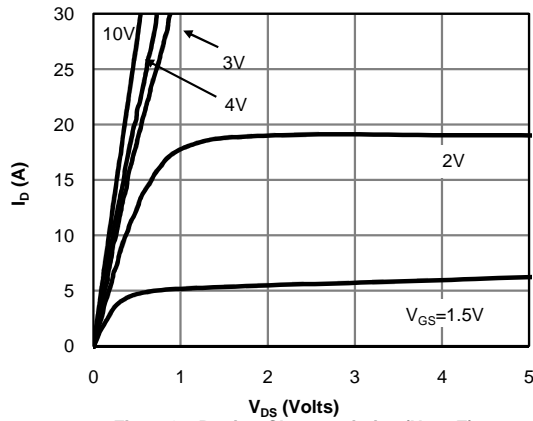


Fig 1: On-Region Characteristics (Note E)

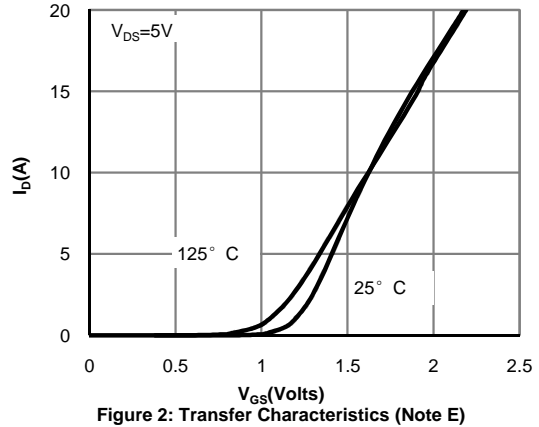


Figure 2: Transfer Characteristics (Note E)

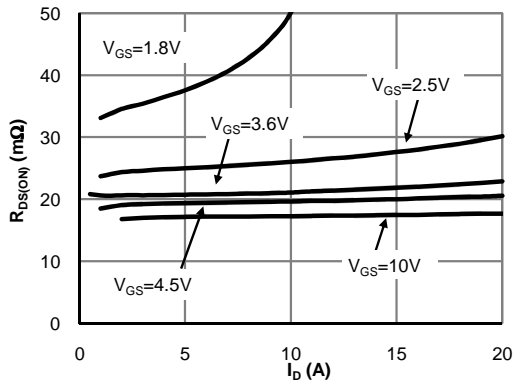


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

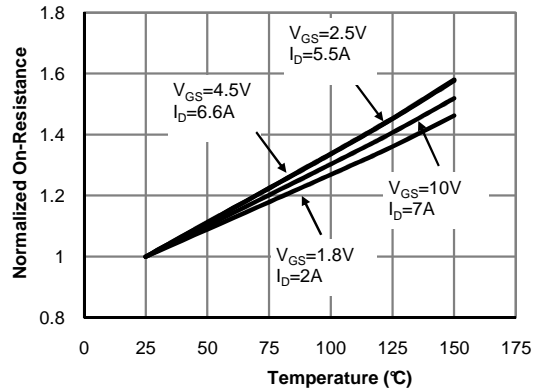


Figure 4: On-Resistance vs. Junction Temperature (Note E)

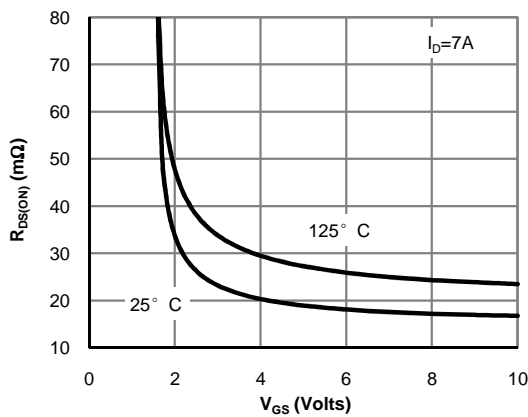


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

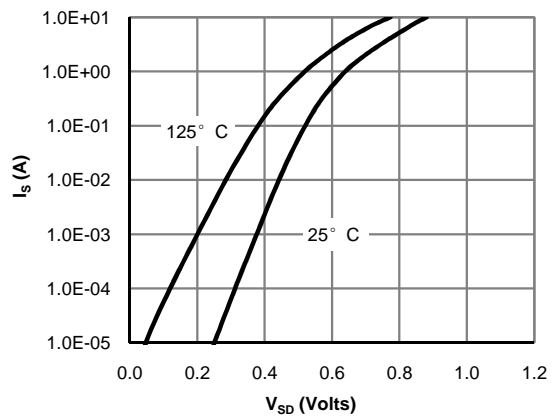


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

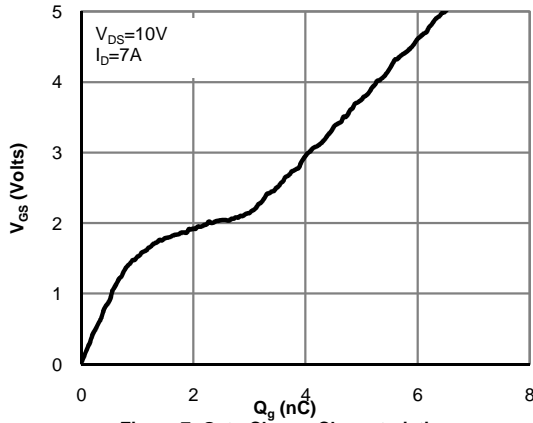


Figure 7: Gate-Charge Characteristics

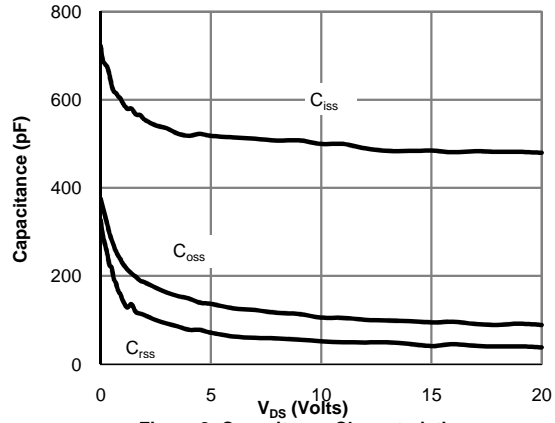


Figure 8: Capacitance Characteristics

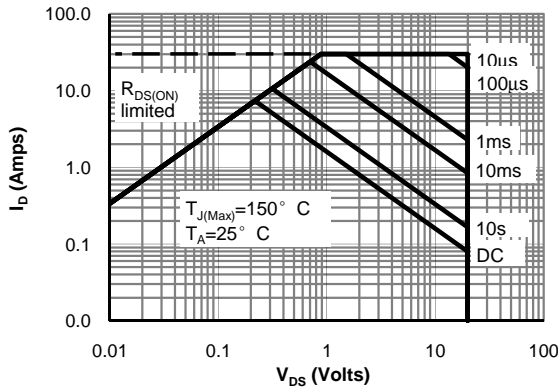


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

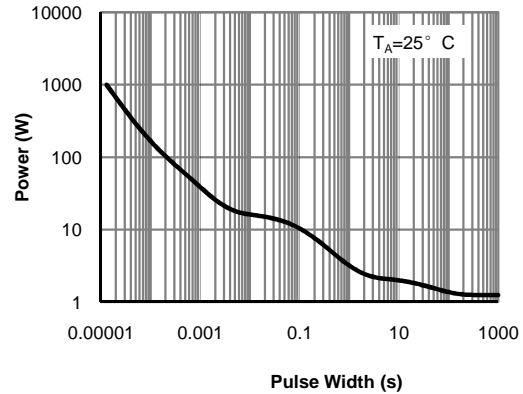


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

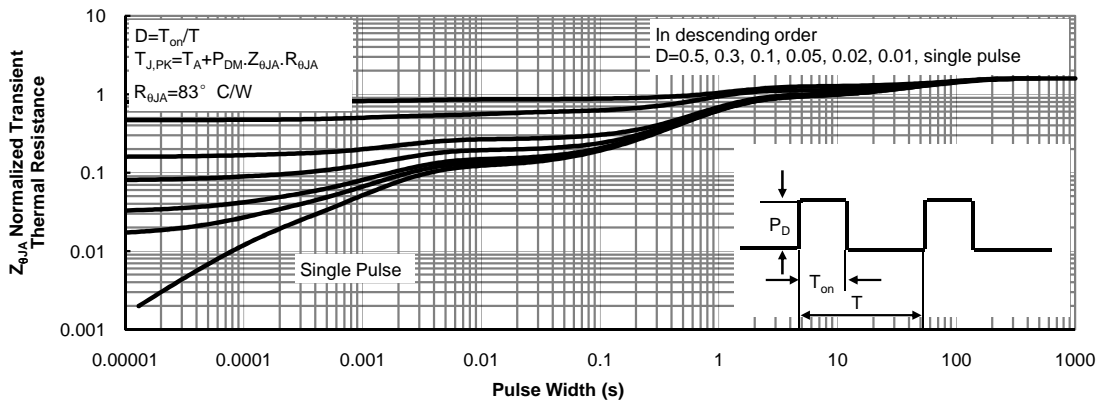
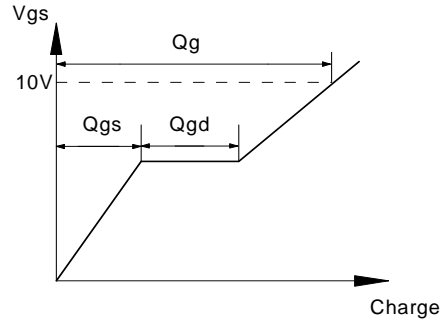
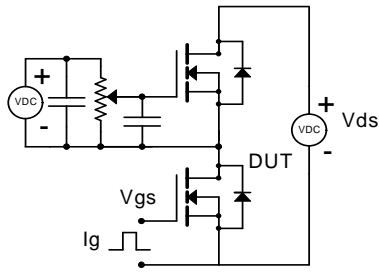
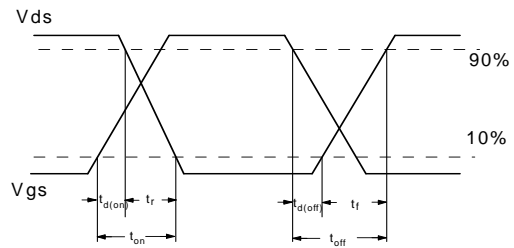
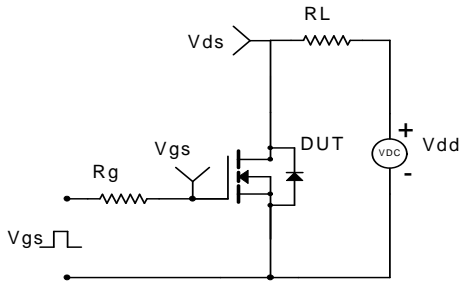


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

